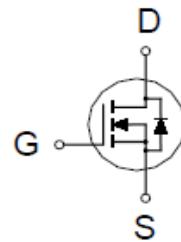
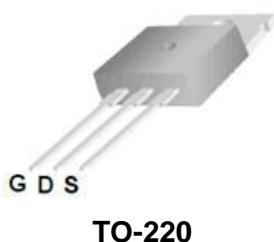


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PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	37mΩ @ $V_{GS} = 10V$	31A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current $T_C = 25^\circ C$	I_D	31	A
$T_C = 100^\circ C$	I_D	20	
Pulsed Drain Current ¹	I_{DM}	75	A
Avalanche Current	I_{AS}	16	
Avalanche Energy ²	E_{AS}	128	mJ
Power Dissipation $T_C = 25^\circ C$	P_D	78	W
$T_C = 100^\circ C$	P_D	21	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		1.6	°C / W

¹Pulse width limited by maximum junction temperature.

²Starting $T_j = 25^\circ C, L = 1mH, V_{DD} = 50V$

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

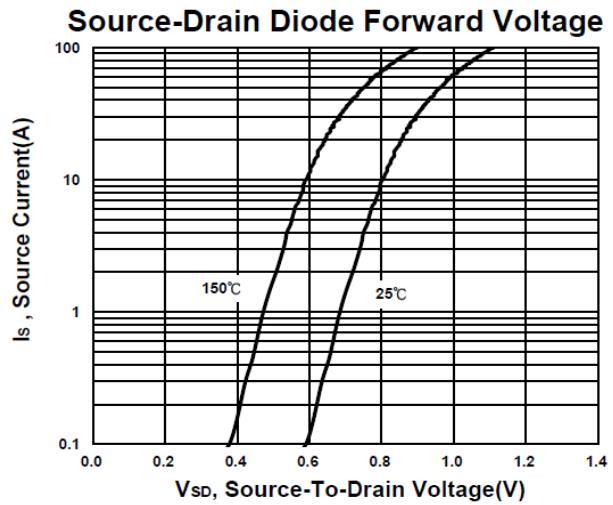
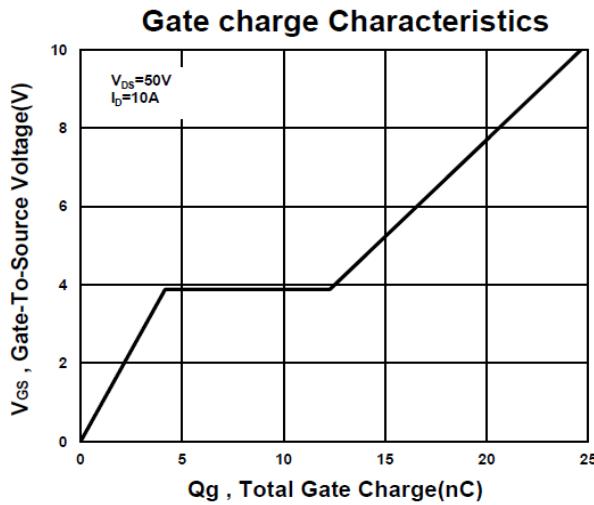
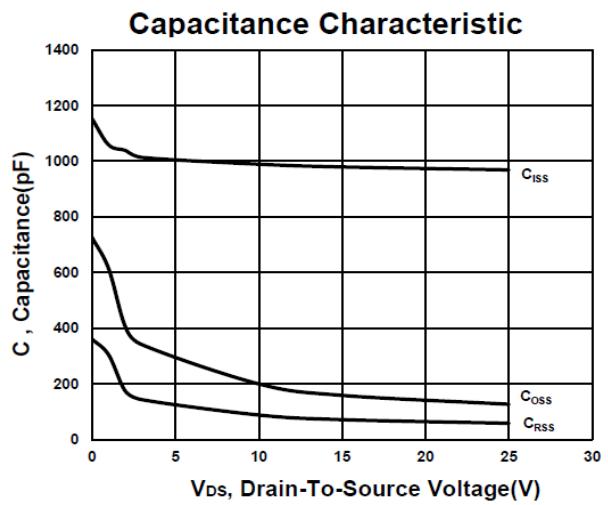
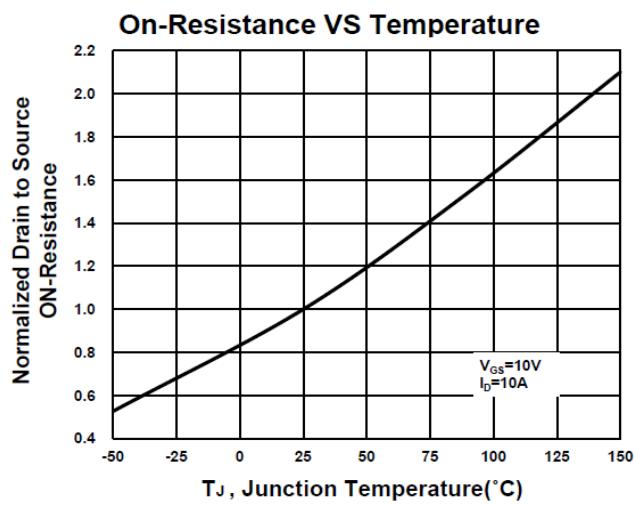
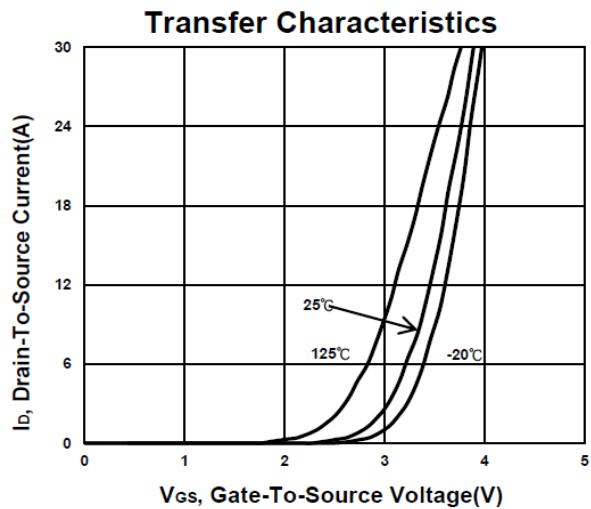
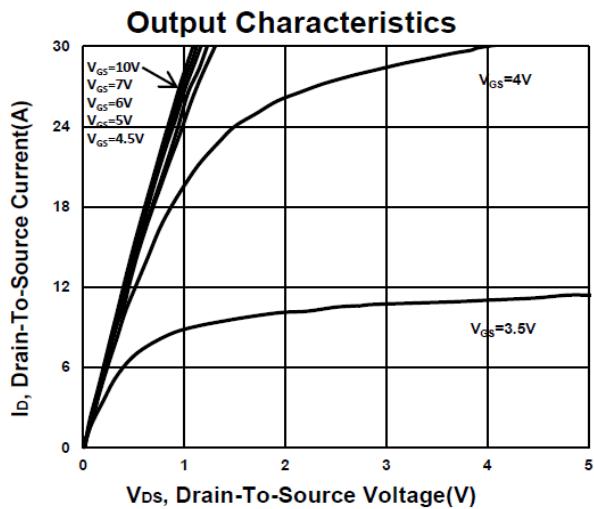
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	100			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1	1.8	3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 80\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
		$V_{\text{DS}} = 80\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$			10	
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 10\text{A}$		35	48	$\text{m}\Omega$
		$V_{\text{GS}} = 10\text{V}, I_D = 10\text{A}$		27	37	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 10\text{V}, I_D = 10\text{A}$		30		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1\text{MHz}$		970		pF
Output Capacitance	C_{oss}			129		
Reverse Transfer Capacitance	C_{rss}			59		
Total Gate Charge ²	Q_g	$V_{\text{DS}} = 50\text{V}, I_D = 10\text{A}, V_{\text{GS}} = 10\text{V}$		25		nC
Gate-Source Charge ²	Q_{gs}			4.3		
Gate-Drain Charge ²	Q_{gd}			8.3		
Turn-On Delay Time ²	$t_{\text{d(on)}}$	$V_{\text{DD}} = 50\text{V}$ $I_D \geq 10\text{A}, V_{\text{GS}} = 10\text{V}, R_{\text{GS}} = 6\Omega$		30		nS
Rise Time ²	t_r			21		
Turn-Off Delay Time ²	$t_{\text{d(off)}}$			45		
Fall Time ²	t_f			21		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current	I_S	$I_F = 10\text{A}, V_{\text{GS}} = 0\text{V}$			31	A
Forward Voltage ¹	V_{SD}				1.2	V
Reverse Recovery Time	t_{rr}			36		nS
Reverse Recovery Charge	Q_{rr}			52		nC

¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

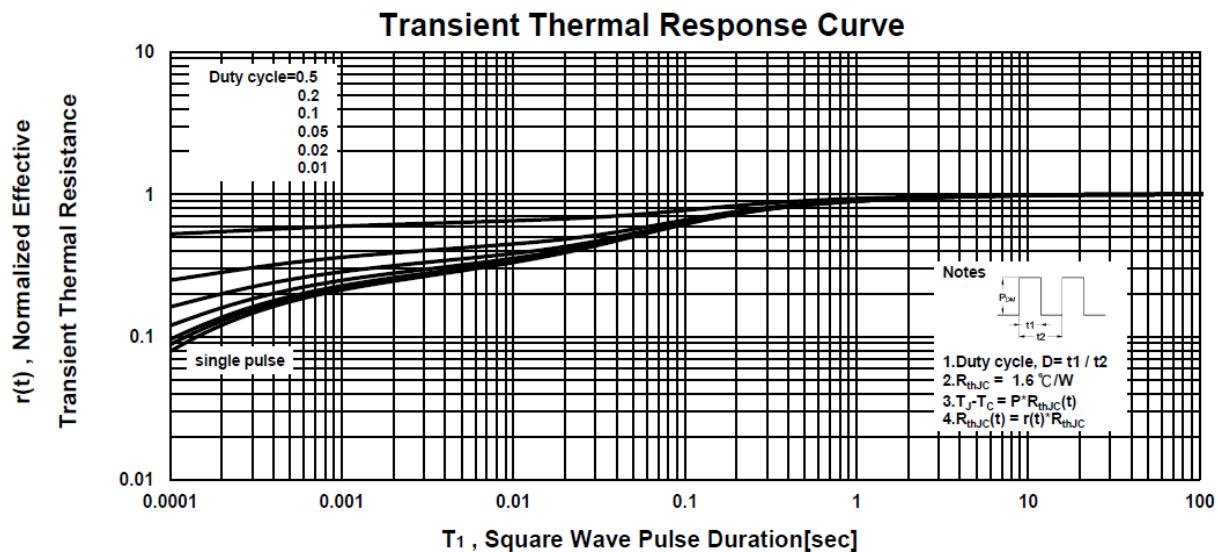
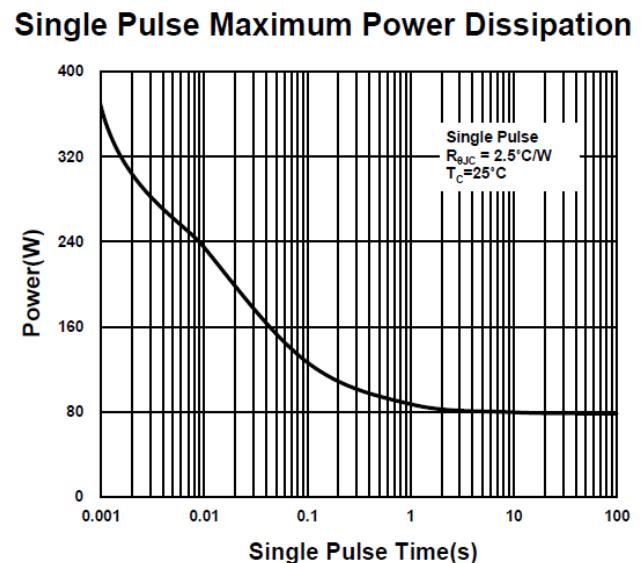
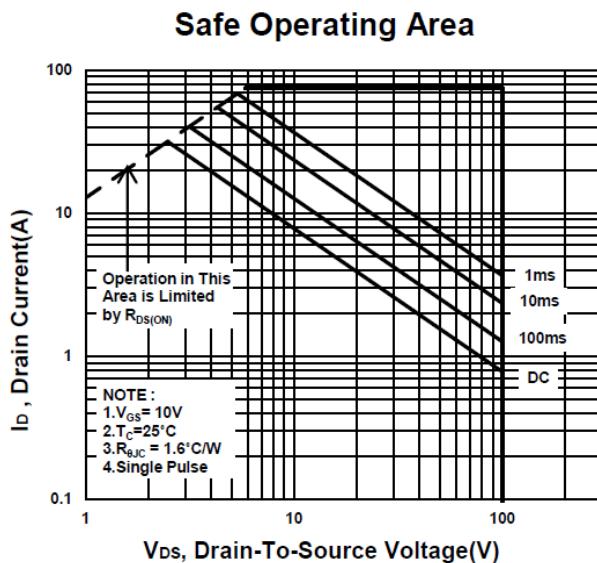
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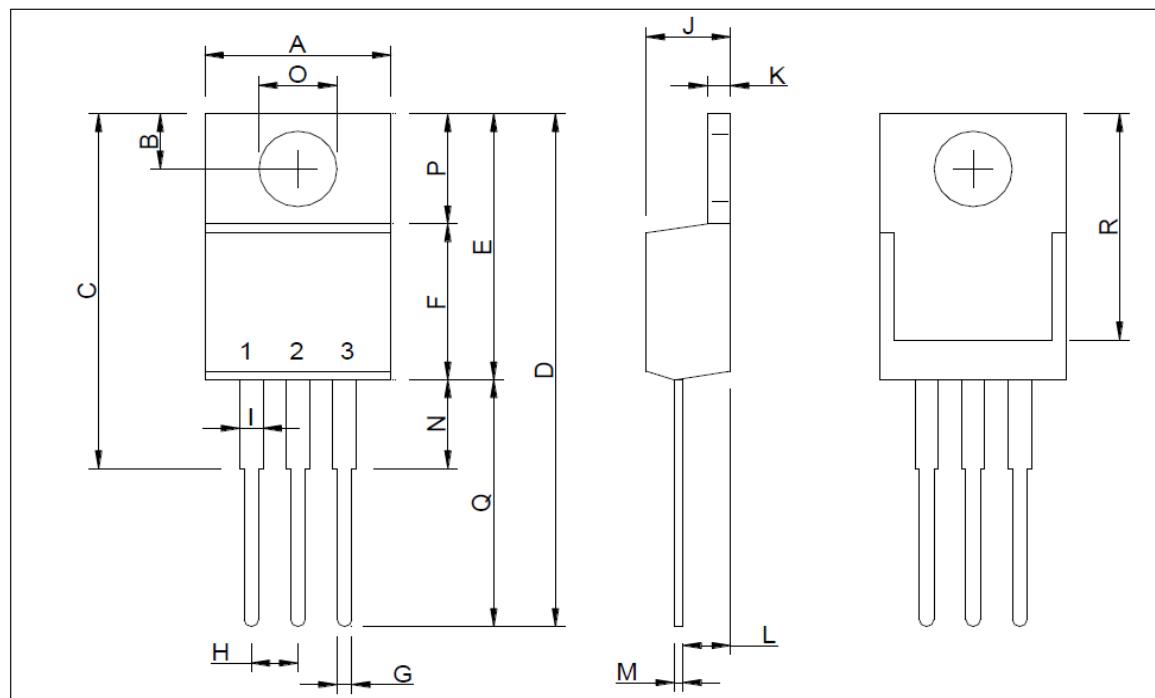
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Package Dimension

TO-220 (3-Lead) MECHANICAL DATA

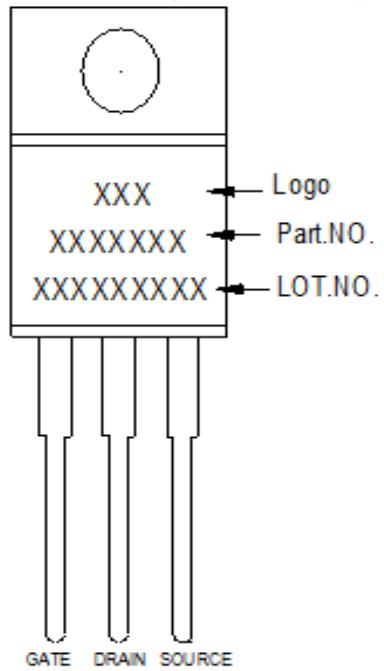
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.65		11.5	J	3.55		4.83
B		2.54		K	1.11		1.45
C	18.1		22.86	L	1.89		3.09
D	26.9		31.24	M	0.34		0.61
E	14.32		16.51	N	2.6		4.06
F	8.38		9.3	O		3.7	
G	0.38		1.02	P	5.84		6.85
H	2.04	2.54	3.04	Q	12.5		14.73
I	1.14		1.8	R	11.3		13.31



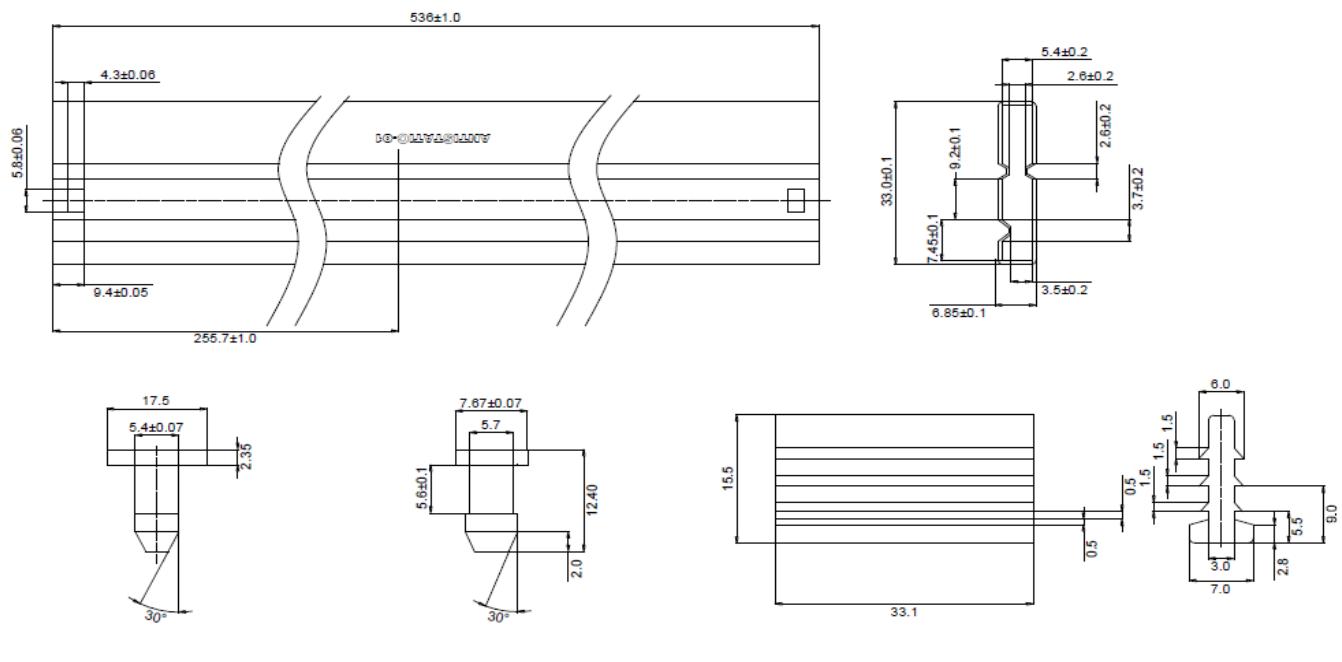
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A. Marking Information



B. Tape&Reel Information: 50pcs/Tube

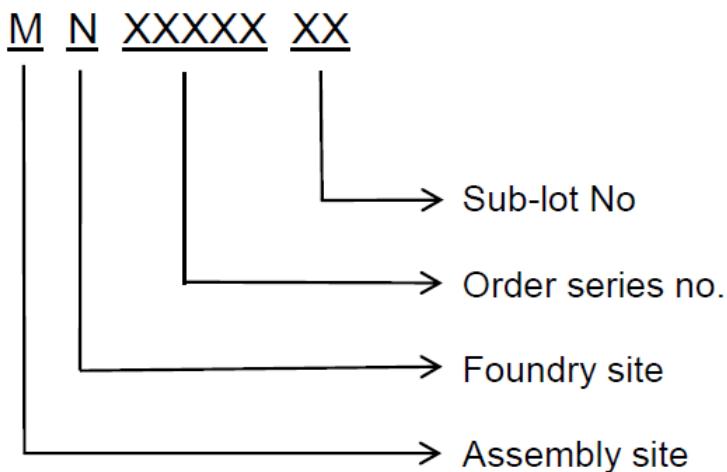


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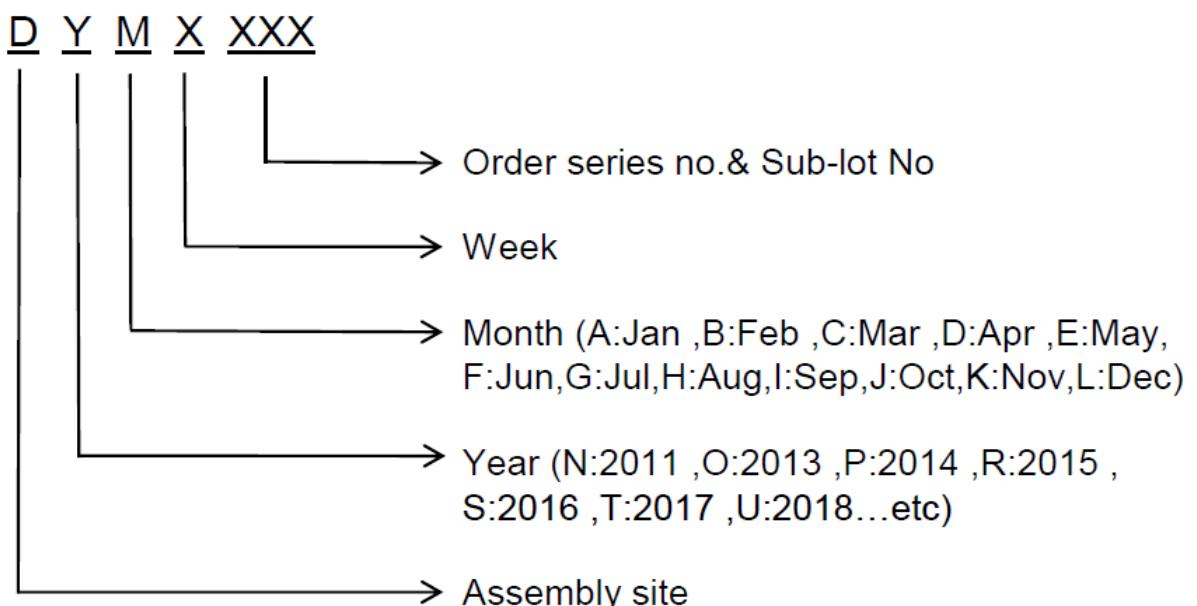
N-Channel Enhancement Mode MOSFET

C. Lot No.&Date Code rule

1. Lot No.



2. Date Code



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D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm			
2	Font style	Times New Roman or Arial (或可区分英文“0”和数字“0”，“G”和“Q”的字型即可)			
3	U-NIKC	Height: 4 mm			
4	Package	Height: 2 mm			
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12			
6	Device	Height: 3 mm (Max: 16 Digit)			
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot			
8	D/C	Height: 3 mm (Max: 7 Digit)			
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed			
10	RoHS label	 long axis: 12 mm minor axis: 6 mm bottom color: White Font color: Black Font style: Arial			
11	Halogen Free label	 Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial			
12	Scan information	Device / Lot / D/C / QTY , Insert “/” between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least			